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	INITIAL	<u> </u>	PEROCUS, PATENTS APPLICATIONS
		1	1 U.S. Patent Application entitled. Method for Improved Cleaning of Substrate Processing System": filed July 11, 1907; Seria No. 08/893,922, Inventors: Kao, et al. 725, 857
) D	for Use with Substrate Processing Systems"; filed April 23, 1997; Serial No. 08/839,111;
	X	Di	Plasma Cleaning Process: filed (2) 3, 1997; Serial No. 08/887,165; Inventors:
		D4	Microwave Plasma Generation, The April 22, 1997; Serial No. 08/839,007; Inventor:
		D5	Generation for Microwave Class Applications"; filed November 13, 1996; Scrial No.
		D6	1. S. Potent Application States. Securely Coupled HDP-CVD Reactor"; filed May 29,
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/ ,		D8	U.S. Patent Application entitled. Apparatus and Methods for Opgraded Substrate Processing System with Microwave Plasme State filed March 5, 1997; Social No. 08/811,627; Inventors: Tanaka et a = 6.039 82 f
	· ·	D9	U.S. Patent Application entitled. Microwave Apparatus for In-situ Vacuum Line Classing for Substrate Processing Equipment', filed October 30, 1996, Serial No. 08/741
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3 0 2003 SHEET (DEPARTMENT OF COMMERCE DOCKET: APPLICATION NO: TENT AND TRADEMARK OFFICE 001945 USA PO3/EYCH/SILICON/JB 09/507,629 INFORMATION DISCLOSURE STATEMENT APPLICANT: SHEN et al. IN AN APPLICATION (Use several sheets if necessary) FILING DATE: GROUP ART UNIT: 02/18/2000 1763 U.S. PATENT DOCUMENTS EXAMINER DOCUMENT NUMBER INITIAL DATE FILING DATE NAME CLASS SUBCLASS IF APPROPRIATE HORI et al. 5384009 5,384,009 1/24/1995 MAK et al. 5180464 5,180,464 1/19/1993 TATSUMI et al 6270 634 6,270,634 8/7/2001 KUMAR et al. 6125 859 6,125,859 10/3/2000 KAO et al. 5,861,233 1/19/1999 SEKINE et al FOREIGN:PATENT DOCUMENTS DOCUMENT NUMBER DATE COUNTRY SUBCLASS ABSTRACT CLASS YE\$ NO OTHER DOCUMENTS (Including Author, Title, Dato, Pertinent Pages, etc.) Kimizuka, Masakatsu et al. "Pattern Profile Control in Magnetron reactive ion etching of Poly-Si." J. Vac. Sci. Technol. B 10(5), Sept/Oct 1992. pp. 2192-2196, EXAMINER: EXAMINER: Initial is reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.